

3A High Performance Step-Up DC/DC Converter

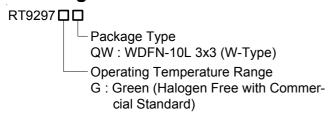
General Description

The RT9297 includes a high performance step-up DC/DC converter that provides a regulated supply voltage for activematrix thin-film transistor (TFT) liquid-crystal displays (LCDs).

The Boost Converter incorporates current mode, fixedfrequency, pulse-width modulation (PWM) circuitry with a built-in N-Channel power MOSFET to achieve high efficiency and fast transient response.

The RT9297 is available in a WDFN -10L 3x3 package

Ordering Information



Note:

Richtek Green products are :

- ▶ RoHS compliant and compatible with the current requirements of IPC/JEDEC J-STD-020.
- ▶ Suitable for use in SnPb or Pb-free soldering processes.

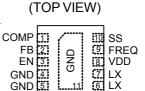
Features

- High Efficiency Up to 90%
- Adjustable Output Voltage: V_{DD} to 24V
- Wide Input Supply Voltage: 2.6V to 5.5V
- Input Under Voltage Lockout
- Pin-Programmable Switching Frequency 640kHz/1.2MHz
- Programmable Soft-Start
- Small 10-Lead WDFN Package
- RoHS Compliant and Halogen Free

Applications

- Notebook Computer Displays
- LCD Monitor Panels
- LCDTV Panels

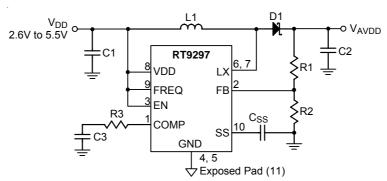
Pin Configurations



WDFN-10L 3x3

GND

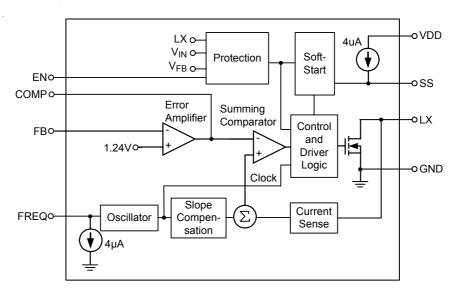
Typical Application Circuit



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Function Block Diagram



Functional Pin Description

Pin No.	Pin Name	Pin Function			
1	COMP	Compensation Pin for Error Amplifier. Connect a series RC from COMP to ground.			
2	FB	Feedback Pin. The feedback regulation voltage is 1.24V nominal. Connect an external resistive voltage-divider between the step-up regulator's output (V _{AVDD}) and GND, with the center tap connected to FB. Place the divider close to the IC and minimize the trace area to reduce noise coupling.			
3	EN	Enable Control Input. Drive EN low to turn off the Boost Converter.			
4, 5 11 (Exposed Pad)	GND	Ground Pin. The exposed pad must be soldered to a large PCB and connected to GND for maximum power dissipation.			
6, 7	LX	Switch Pin. LX is the drain of the internal MOSFET. Connect the inductor/rectifier diode junction to LX and minimize the trace area for lower EMI.			
8	VDD	Supply Pin. Bypass V_{DD} with a minimum $1\mu F$ ceramic capacitor directly to GND.			
9	FREQ	Frequency-Select Input. When FREQ is low, the oscillator frequency will be set to 640kHz. When FREQ is high, the frequency will be set to 1.2MHz. This input has a $6\mu\text{A}$ pull-down current.			
10	SS	Soft-Start Control Pin. Connect a soft-start capacitor (C_{SS}) to this pin. A 4 μ A constant current charges the soft-start capacitor. When EN connected to GND, the soft-start capacitor is discharged. When EN connected to V_{DD} high, the soft-start capacitor is charged to V_{DD} . Leave floating for not using soft-start.			



Absolute Maximum Ratings (Note 1)

• LX to GND	−0.3V to 26V
• Other Pins to GND	- −0.3V to 6V
 Power Dissipation, P_D @ T_A= 25°C 	
WDFN-10L 3x3	- 1.667W
Package Thermal Resistance (Note 2)	
WDFN-10L 3x3, θ_{JA}	- 60°C/W
WDFN-10L 3x3, θ_{JC}	- 8.2°C/W
• Lead Temperature (Soldering, 10 sec.)	- 260°C
Junction Temperature	- 150°C
Storage Temperature Range	– –65°C to 150°C
ESD Susceptibility (Note 3)	
HBM (Human Body Mode)	- 2kV
MM (Machine Mode)	- 200V
Recommended Operating Conditions (Note 4)	

Electrical Characteristics

 $(V_{DD} = 3.3V. T_A = 25^{\circ}C. \text{ unless otherwise specified})$

Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit
Supply Current	•		•			
Input Voltage Range	V _{DD}	V _{AVDD} < 18V	2.6		5.5	V
		18V < V _{AVDD} < 24V	4		5.5	
Output Voltage Range	V_{AVDD}		V_{DD}		24	V
Under-Voltage Lockout	Vuvlo	V _{DD} Rising		2.4		V
Threshold		Hysteresis		50		mV
Quicacent Current	lQ	V _{FB} = 1.3V, LX Not Switching	-	0.5	1	mA
Quiescent Current		V _{FB} = 1V, LX Switching		4		
Shutdown Current	ISHDN	EN = GND		0.1	10	μΑ
Oscillator						
Oscillator Francisco	fosc	FREQ = GND	500	640	750	kHz
Oscillator Frequency		FREQ = V _{IN}	1000	1240	1500	
Maximum Duty Cycle				90		%
Error Amplifier						
Feedback Regulation Voltage	V _{FB}		1.22	1.24	1.26	V
Feedback Input Bias Current	I _{FB}			125	250	nA
Feedback Line Regulation				0.05	0.2	%/V
Transconductance	Gm	$\Delta I = \pm 2.5 \mu A$ at COMP = 1V		135	1	μΑ/V
Voltage Gain	Av	FB to COMP		700		V/V

To be continued

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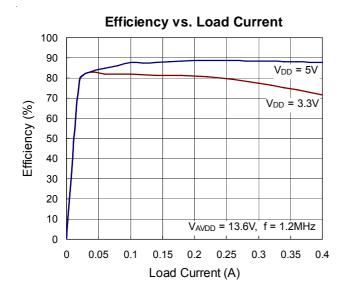
Parameter	Symbol	Test Conditions	Min	Тур	Max	Unit	
N-Channel MOSFET							
Current Limit	I _{LIM}		3	3.8	5	Α	
On-Resistance	R _{DS(ON)}			125	250	mΩ	
Leakage Current	I _{LEAK}	V _L X = 24V		30	45	μΑ	
Current-Sense Transresistance	R _{CS}			0.25		V/A	
Soft-Start							
Charge Current	ISS			4		μΑ	
Control Inputs							
EN, FREQ Input Low Voltage	V _{IL}				0.3 x V _{DD}	V	
EN, FREQ Input High Voltage	V _{IH}		0.7 x V _{DD}			V	
EN, FREQ Input Hysteresis				0.1 x V _{DD}		V	
FREQ Pull-down Current				6		μΑ	
EN Input Current	I _{EN}	EN = GND		0.001	1	μΑ	

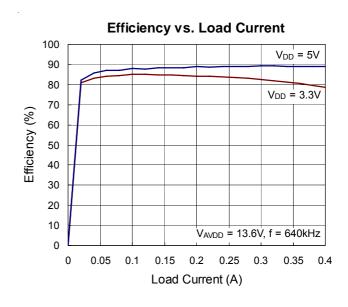
- **Note 1.** Stresses listed as the above "Absolute Maximum Ratings" may cause permanent damage to the device. These are for stress ratings. Functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may remain possibility to affect device reliability.
- Note 2. θ_{JA} is measured in the natural convection at $T_A = 25^{\circ}C$ on a high effective four layers thermal conductivity test board of JEDEC 51-7 thermal measurement standard. The case point of θ_{JC} is on the exposed pad for the package.
- Note 3. Devices are ESD sensitive. Handling precaution is recommended.
- Note 4. The device is not guaranteed to function outside its operating conditions.

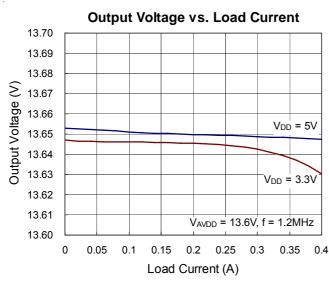
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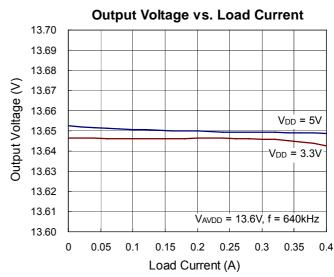


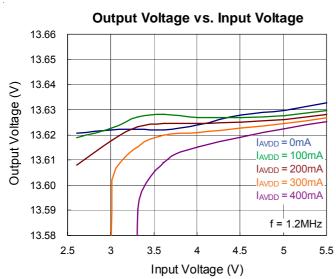
Typical Operating Characteristics

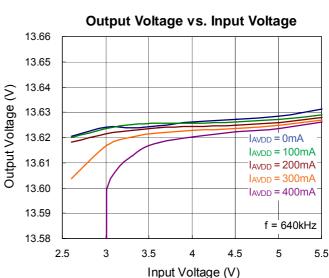








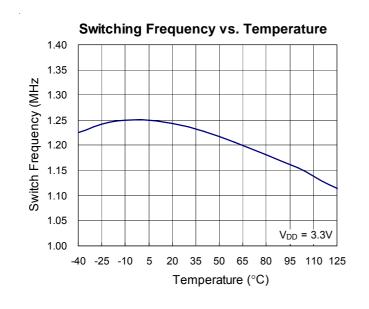


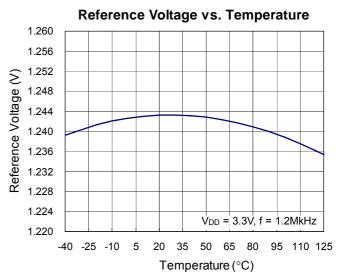


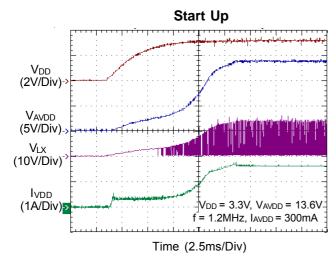
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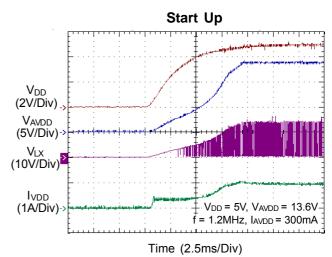
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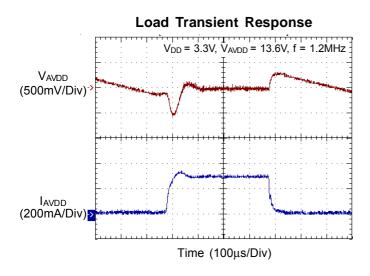


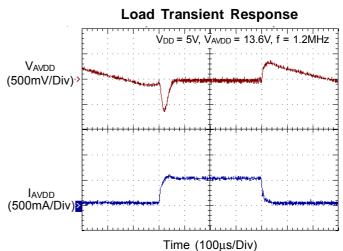












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Application Information

The RT9297 contains a high performance boost regulator to generate voltage for the panel source driver ICs. The following content contains the detailed description and the information of component selection.

Boost Regulator

The boost regulator is a high efficiency current-mode PWM architecture with 640K / 1.2MHz operation frequency. It performs fast transient responses to generate source driver supplies for TFT LCD display. The high operation frequency allows smaller components used to minimize the thickness of the LCD panel. The output voltage setting can be achieved by setting the resistive voltage-divider sensing at FB pin. The error amplifier varies the COMP voltage by sensing the FB pin to regulate the output voltage. For better stability, the slope compensation signal summed with the current-sense signal will be compared with the COMP voltage to determine the current trip point and duty cycle.

Soft-Start

The RT9297 provides soft-start function to minimize the inrush current. When power on, an internal constant current charges an external capacitor. The rising voltage rate on the COMP pin is limited during the charging period and the inductor peak current will also be limited at the same time. When power off, the external capacitor will be discharged for next soft start time.

The soft-start function is implemented by the external capacitor with a $4\mu A$ constant current charging to the soft-start capacitor. Therefore, the capacitor should be large enough for output voltage regulation. Typical value for soft-start capacitor range is 33nF. The available soft-start capacitor range is from 10nF to 100nF.

Output Voltage Setting

The regulated output voltage is shown as following equation:

$$V_{AVDD} = 1.24V \times \left(1 + \frac{R_1}{R_2}\right)$$

The recommended value for R2 should be up to $10k\Omega$ without some sacrificing. To place the resistor divider as close as possible to the chip can reduce noise sensitivity.

Loop Compensation

The voltage feedback loop can be compensated with an external compensation network consisted of R_{COMP} and C_{COMP} . Choose R_{COMP} to set high frequency integrator gain for fast transient response and C_{COMP} to set the integrator zero to maintain loop stability. For typical application $V_{DD}=3.3V$, $V_{AVDD}=13.6V$, $C4=4.7\mu F \times 3$, $L=3.6\mu H$, the recommended value for compensation is as below : $R_{COMP}=56k\Omega$, $C_{COMP}=330pF$.

Over Current Protection

The RT9297 boost converter has over-current protection to limit peak inductor current. It prevents large current from damaging the inductor and diode. During the ON-time, once the inductor current exceeds the current limit, the internal LX switch turns off immediately and shortens the duty cycle. Therefore, the output voltage drops if the over-current condition occurs. The current limit there should is also affected by the input voltage, duty cycle and inductor value.

Over Temperature Protection

The RT9297 boost converter has thermal protection function to prevent the chip from overheating. When the junction temperature exceeds 155°C, it will shut down the device. Once the device cools down by approximately 30°C, it will start to operate normally. For continuous operation, do not operate over the maximum junction temperature rating 125°C.

Inductor Selection

The inductance depends on the maximum input current. The inductor current ripple is 20% to 40% of maximum input current that is a general rule. Assume, choose 40% as the criterion then

$$I_{VDD(MAX)} = \frac{V_{AVDD} \times I_{AVDD(MAX)}}{n \times V_{DD}}$$

 $I_{RIPPLE} = 0.4 \times I_{VDD(MAX)}$

Where η is the efficiency, $I_{\text{IN(MAX)}}$ is the maximum input current, I_{RIPPLE} is the inductor current ripple. Beside, the input peak current is maximum input current plus half of inductor current ripple.

 $I_{PEAK} = 1.2 \times I_{VDD(MAX)}$

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Note that the saturated current of inductor must be greater than I_{PEAK} . The inductance can be eventually determined as follow equation:

$$L = \frac{\eta x (V_{DD})^2 x (V_{AVDD}-V_{DD})}{0.4 x (V_{AVDD})^2 x I_{AVDD(MAX)} x f_{OSC}}$$

Where f_{OSC} is the switching frequency. To consider the system performance, a shielded inductor is preferred to avoid EMI issue.

Diode Selection

Schottky diode is a good choice for an asynchronous Boost converter due to the small forward voltage. However, power dissipation, reverse voltage rating and pulsating peak current are the important parameters for Schottky diode selection. It is recommended to choose a suitable diode whose reverse voltage rating is greater than the maximum output voltage.

Output Capacitor Selection

Output voltage ripple is an important index for estimating the performance. This portion consists of two parts, one is the product of inductor current ripple and ESR of the output capacitor, another part is formed by charging and discharging process of output capacitor. Evaluate ΔV_{AVDD} by ideal energy equalization. According to the definition of Ω :

$$Q = \frac{1}{2} \left(\frac{1}{2} \Delta I_L \times \frac{1}{2} T_S \right) = C4 \times \Delta V_{AVDD}$$

Where T_S is the inverse of switching frequency and the ΔI_L is the inductor current ripple. Move C4 to left side to estimate the value of ΔV_{AVDD} as

$$\Delta V_{AVDD} = \frac{\Delta I_L \times T_S}{8 \times C4}$$

And the output voltage ripple can be determined as

$$\Delta V_{AVDD} = \Delta I_L \times ESR + \frac{\Delta I_L \times T_S}{8 \times C4}$$

Input Capacitor Selection

Low ESR ceramic capacitors are recommended for input capacitor applications. Low ESR will effectively reduce the input voltage ripple caused by switching operation. A $10\mu F$ is sufficient for most applications. Nevertheless, this value can be decreased for lower output current requirement. Another consideration is the voltage rating of the input capacitor must be greater than the maximum input voltage.

Thermal Considerations

For continuous operation, do not exceed absolute maximum operation junction temperature. The maximum power dissipation depends on the thermal resistance of IC package, PCB layout, the rate of surroundings airflow and temperature difference between junction to ambient. The maximum power dissipation can be calculated by following formula:

$$P_{D(MAX)} = (T_{J(MAX)} - T_A) / \theta_{JA}$$

Where $T_{J(MAX)}$ is the maximum operation junction temperature 125°C, T_A is the ambient temperature and the θ_{JA} is the junction to ambient thermal resistance.

For recommended operating conditions specification, where $T_{J(MAX)}$ is the maximum junction temperature of the die (125°C) and T_A is the maximum ambient temperature. The junction to ambient thermal resistance θ_{JA} is layout dependent. For WDFN-10L 3x3 packages, the thermal resistance θ_{JA} is 36°C/W on the standard JEDEC 51-7 four layers thermal test board. The maximum power dissipation at T_A = 25°C can be calculated by following formula:

$$P_{D(MAX)}$$
 = (125°C - 25°C) / (60°C/W) = 1.667 W for WDFN-10L 3x3 packages

The maximum power dissipation depends on operating ambient temperature for fixed $T_{J(MAX)}$ and thermal resistance θ_{JA} . For WDFN-10L 3x3 package, the Figure 1 of derating curves allows the designer to see the effect of rising ambient temperature on the maximum power allowed.

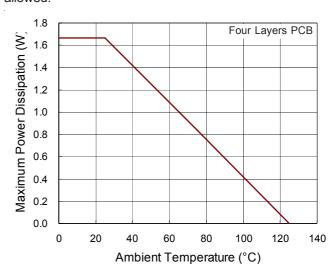


Figure 1. Derating Curve for RT9297 Package



Layout Considerations:

For high frequency switching power supplies, the PCB layout is important to get good regulation, high efficiency and stability. The following descriptions are the guidelines for better PCB layout.

- ▶ For good regulation, place the power components as close as possible. The traces should be wide and short enough especially for the high-current output loop.
- ▶ The feedback voltage-divider resistors must be near the feedback pin. The divider center trace must be shorter and the trace must be kept away from any switching nodes.
- ▶ The compensation circuit should be kept away from the power loops and be shielded with a ground trace to prevent any noise coupling.
- ▶ Minimize the size of the LX node and keep it wide and shorter. Keep the LX node away from the FB.
- ▶ The exposed pad of the chip should be connected to a strong ground plane for maximum thermal consideration.

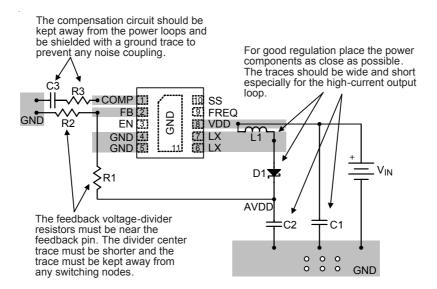
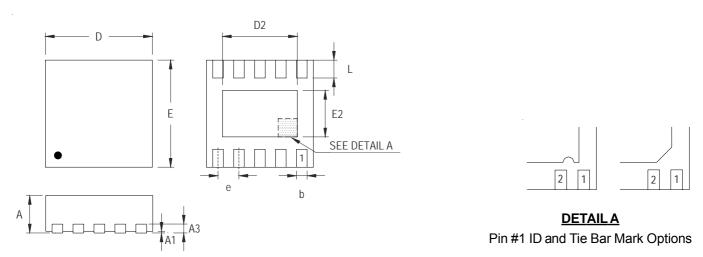


Figure 2. PCB Layout Guide

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Outline Dimension



Note: The configuration of the Pin #1 identifier is optional, but must be located within the zone indicated.

Symbol	Dimensions I	n Millimeters	Dimensions In Inches		
	Min	Max	Min	Max	
А	0.700	0.800	0.028	0.031	
A1	0.000	0.050	0.000	0.002	
A3	0.175	0.250	0.007	0.010	
b	0.180	0.300	0.007	0.012	
D	2.950	3.050	0.116	0.120	
D2	2.300	2.650	0.091	0.104	
Е	2.950	3.050	0.116	0.120	
E2	1.500	1.750	0.059	0.069	
е	0.5	500	0.0)20	
Ĺ	0.350	0.450	0.014	0.018	

W-Type 10L DFN 3x3 Package

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